AK93C46 Series

1024-BIT SERIAL (5V ONLY) CMOS ELECTRICALY ERASABLE PROGRAMMABLE MEMORY

FEATURES

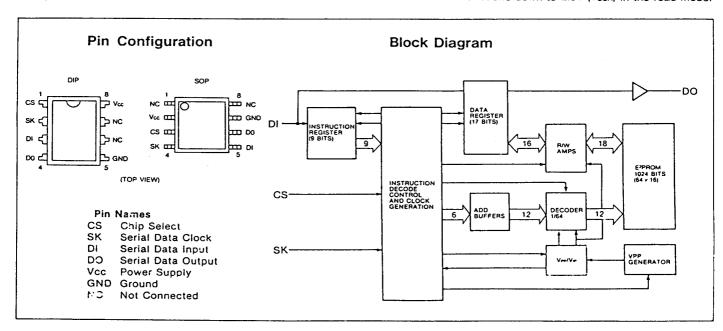
- **MADVANCED CMOS E2PROM TECHNOLOGY**
- **TREAD/WRITE NON-VOLATILE MEMORY**
 - -Single 5V supply operation
 - -1024 bits, 64×16 organization
- Easy to use yet versatile serial data interface
- **ILOW POWER CONSUMPTION**
 - -3mA Max Active
 - -1mA Max Standby, TTL interface
 - -100µA Max Standby, CMOS interface
- **ESPECIAL FEATURES**
 - -Automatic write cycle time-out
 - -Ready/Busy status signal
 - -Software controlled write protection
- **ILOW VOLTAGE READ OPERATION**
 - -Vccn=2.8Vmin (AK93C46M/MF)

- **MIDEAL FOR LOW DENSITY DATA STORAGE**
 - -Low cost, space saving, 8-pin package
 - Interfaces with popular microcontrollers and standard microprocessors
- **MAPPLICATION VERSATILITY**
 - Alarm Devices, Electronic Locks, Appliances, Terminals, Smart Cards, Satellite Receivers, Robotics, Meters, Telephones, Tuners, etc.
- **SUPER-SET COMPATIBILITY**
 - -National: NMC9306/COP494, NMC9346/COP495
 - -General Instrument : ER59256, ER5911
 - -NCR: 59306, 5930B

GENERAL DESCRIPTION

The AK 93 C46 is a 1024-bit, 5V-only, serial, read/write, non-volatile memory device fabricated using an advanced CMOS E²PROM technology. Its 1024 bits of memory are organized into 64 registers of 16 bits each. Each register is individually addressable for serial read or write operations. A versatile serial interface, consisting of chip select, clock, data-in and data-out, can easily be controlled by popular microcontrollers or standard microprocessors.

Low power consumption, low cost, and space efficiency make the 'AK93C46 an ideal candidate for high volume, low density, data storage applications. Special features of the AK93C46 include: automatic write time-out, ready/busy status signal, software controlled write protection and ultra-low standby power mode when deselected (CS low). Additionally AK93C46 offers functional compatibility with existing NMOS serial E²PROMs. AK93C46M/MF functions down to 2.8V (Vccn) in the read mode.



FUNCTIONAL DESCRIPTION

Device Operation 1,2,3

The AK93C46 is a serial 1024 bit peripheral memory device intended for use in non-volatile data storage applications. Its memory organization consists of 64 registers, each 16-bits wide. Each register is independently addressable for read or write operations. Six 9-bit serial instructions are used to control the operation of the AK93C46. These instructions are serially clocked into the DI input as controlled by the CS and SK inputs.

The instructions include read, write, erase, erase/write enable, erase/write disable and erase all registers. The format of each instruction has a logical "1" as a start bit, two bits as an op code, and six bits of address. During read operations the DO output is valid as data out after the address is entered. After a write/erase instruction, the DO output serves as a ready/busy status indicator signaling when the operation is complete allowing further read or write access. The ready/busy status indicator is only valid when CS is active (high), when CS is low, the DO output goes into a high impedance state. After a new instruction is initiated, the DO output also goes to high impedance.

Read

The read instruction is the only instruction which outputs serial data on the DO pin. After a read instruction is received, the instruction and address are decoded, followed by data transfer from the memory register into a 16-bit serial-out-shift register. A dummy bit (logical "0") precedes the 16-bit data output string. The output data changes during the high states of the system clock.

Erase/Write Enable and Disable

When Vcc is applied to the part it powers up in the programming disable (EWDS) state, programming must be preceded by a programming enable (EWEN) instruction. Programming remains enabled until a programming disable (EWDS) instruction is executed or Vcc is removed from the part. The programming disable instruction is provided to protect against accidental data disturb.

Execution of a read instruction is independent of both EWEN and EWDS instructions.

Frase

Like most EEPROMs, the register must first be erased (all bits set to logical "1") before the register can be written (certain bits set to logical "0"). After an erase instruction is input, 'CS is dropped low. This falling edge of CS determines the start of the self-timed programming cycle. If CS is brought high subsequently (after observing the Tcs specification), the DO pin will indicate the ready/busy status of the chip. The DO pin will go low if the chip is still programming. The DO pin will go high when all bits of the register at the address specified in the instruction have been set to a logical "1". The part is now ready for the next instruction sequence.

Write

The write instruction is followed by 16 bits of data to be written into the specified address. After the last bit of data is put on the data in (DI) pin, CS must be brought low before the next rising edge of the SK clock. This falling edge of CS initiates the self-timed programming cycle. Like all programming modes, DO indicates the ready/busy status of the chip if CS is brought high after a minimum of $1\mu s$ (Tcs). DO=logical "0" indicates that programming is still in progress. DO=logical "1" indicates that the register at the address specified in the instruction has been written with the data pattern specified in the instruction and the part is ready for another instruction. The register to be written into must have been previously erased.

Chip Erase

Entire chip erasing is provided for ease of programming. Erasing the chip means that all registers in the memory array have each bit set to a logical "1". Each register is then ready for write instruction. The chip erase cycle is identical to the erase cycle except for the different op code.

Instruction Set For 93C46

Instruction	Start Bit	Opcode	Address	Data	Comments
READ	01	10	A5A4A3A2A1A0		READ register A5A4A3A2A1A0
WRITE	01	01	A5A4A3A2A1A0	D ₁₅ -D ₀	WRITE register A5A4A3A2A1A0
ERASE	01	11	A5A4A3A2A1A0	1	ERASE register A5A4A3A2A1A0
EWEN	01	00	11XXXX		ERASE/WRITE enable
EWDS	21	00	ooxxxx	1	ERASE/WRITE disable
ERAL	01	00	10XXXX	1	Erase all registers
WRAL	01	00	01XXXX	D ₁₅ -D ₀	Write all registers4

AK93C46 has 7 instructions as shown. Note that the Most Significant Bit of any given instruction is a "1" and is viewed as a start bit in the interface sequence. The next 8 bits carry the op code and the 6-bit address for 1 of 64, 16-bit registers.

Notes

- ¹ CS must be brought low for a minimum of 1µs (Tcs) between consecutive instruction cycles.
- ² During a programming mode (write, erase, chip erase), SK clock is only needed while the actual instruction, i.e. start bit, op code address and data is being input. It can remain deactivated during the self-timed programming cycle and status check.
- ³ DI must be brought low during the self-timed programming cycle and status check.
- ⁴ The write-all (WRAL) command writes all registers to a logical 0. This command is provided for device evaluation purposes only and is not meant to be used for normal operation.
- ⁵ Stress above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum conditions for extended periods may affect device reliability.



ABSOLUTE MAXIMUM RATINGS⁵

Voltage relative to ground Ambient operating temperature -0.3V to +6.5V -30°C to +70°C Ambient storage temperature

Lead temperature (soldering 10 sec.)

-65°C to +125°C

+260°C

D.C. AND A.C. ELECTRICAL CHARACTERISTICS

 $T_A = -30$ °C to +70°C, Vcc = 5V + 10% unless otherwise specified

Symbol	Parameter	Conditions	MIN	MAX	UNIT
Vcc	Operating Voltage		4.5	5.5	٧
lcc	Operating Current TTL/CMOS Inputs	V _{CC} =5.5V, CS=SK=V _{IH} DO=OPEN, f=250 KHz		3	mA
lccs81	Standby Current TTL/CMOS Inputs	V _{CC} =5.5V, CS=V _{IL} DO=OPEN		1	mA
Iccs82	Standby Current CMOS Inputs	Vcc=5.5V, CS=V _{IL} , DO=OPEN Inputs=Vcc or GND		100	μА
VIL	Input Voltage Low		-0.1	0.8	٧
ViH	Input Voltage High		2.0	Vcc+1	V
Vol	Output Voltage Low	ioL=2.1mA		0.4	٧
Vон	Output Voltage High	loн=0.4mA	2.2		V
lu	Input Leakage Current	V _{IN} =5.5V		10	μА
ILO	Output Leakage Current	V _{OUT} =5.5V, CS=0,		10	μА
fsĸ	SK Frequency		0	250	kHz
	SK Duty Cycle		25	75	%
tcss	Chip Select High to Serial Clock High Delay		200		ns
tсsн	Serial Clock Low to Chip Select Low Delay		О		ns
tois	Data Setup Time (Write)		400		ns
tоін	Data Hold Time (Write)		400		ns
t _{PD1}	Serial Clock to Output Delay	CL=100PF, VoL=0.8V, VoH=2.0V		2	μS
tpoo	Serial Glock to Gulput Delay	V _{IL} =0.45V, V _{IH} =2.4V, C _L =100PF		2	μS
te/w	Self-timed Program Cycle			10	ms
tcs	Min CS Low Time		1		μS
tsv	CS to Status Valid	CL=100PF		1	μS
toн tıн	Falling Edge of CS to DO High Impedance			400	ns

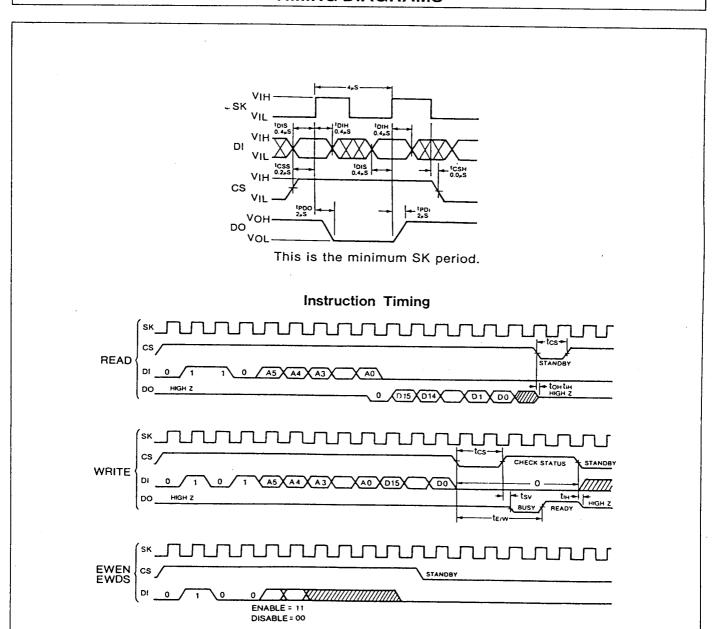
The following characteristics apply only for the READ operation of AK93C46M/MF

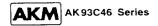
Symbol	Paramets:	Conditions	MIN	MAX	UNIT
VCCR	Operating Voltage For Read		2.8		V
VILR	Input Voltage Low			0.6	V
Viha	Input Voltage High	Vcca=2.8V	1.8		V
VOLR	Output Voltage Low	V _{CCR} =2.8V loL=2.1mA		0.4	V
Vohr	Output Voltage High	Vccn=2.8V IoH=0.1mA	1.8		٧
t _{PD1R}	Serial Clock to	Vot=0.6V, VoH=1.8V, VIL=0.45V		2	μS
tPO2R	PD2R Output Delay	V _H =2.0V, CL=100PF, V _{CCR} =2.8V		2	μS

NON-VOLATILE CHARACTERISTICS

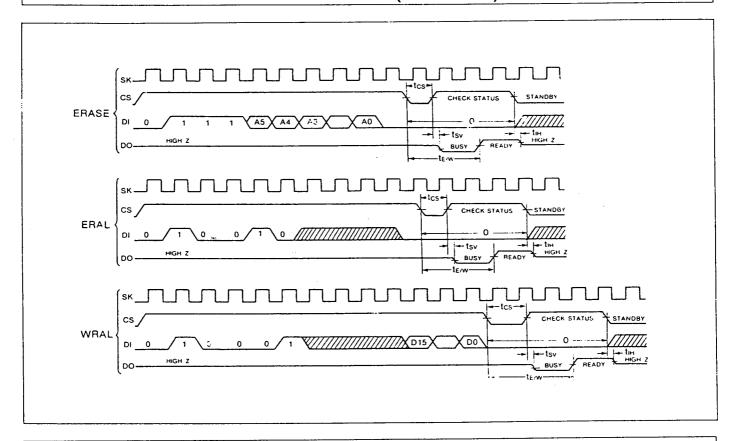
Symbol	Parameter	Condition	
Ton	Data Retention Time	Ta=70°C	10 years (min.)
New	Write/Erase Cycles		10 ⁴ (typ.)

TIMING DIAGRAMS





TIMING DIAGRAM (Continued)

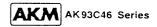


ORDER GUIDE

DEVICE	TEMP.RANGE	Vcc min. (Read)	Vcc min. (Write)	PACKAGE
AK93C46	-30°C∼+70°C	+4.5V	+4.5V	8PinDIP
AK93C46F	-30°C∼+70°C	+4.5V	+4.5V	8PinSOP
AK93C46M	-30°C~+70°C	+2.8V	+4.5V	8PinDIP
AK93C46MF	-30°C∼+70°C	+2.8V	+4.5V	8PinSOP

OPERATING CONDITIONS

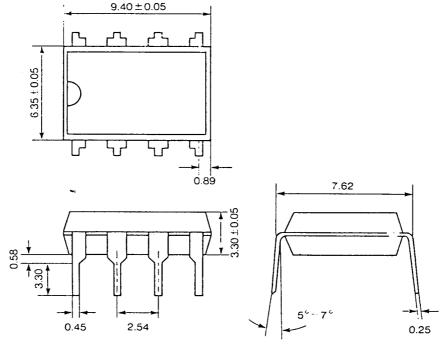
Temperature Range			–30°C to +70°C	
Vcc Power Supply	Write		4.5~5.5V	
	Read	93C46/F	4.5~5.5V	
		93C46M/MF	2.8~5.5V	



OUTLINE DIMENSIONS

AK93C46/M

(UNIT: mm)



AK93C46F/MF

